

Fig.1

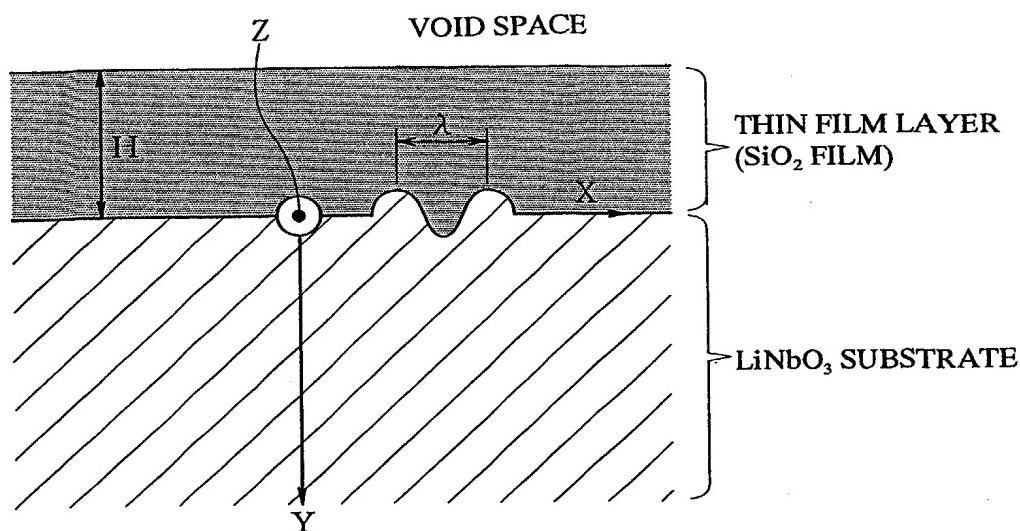


Fig.2
(10°)

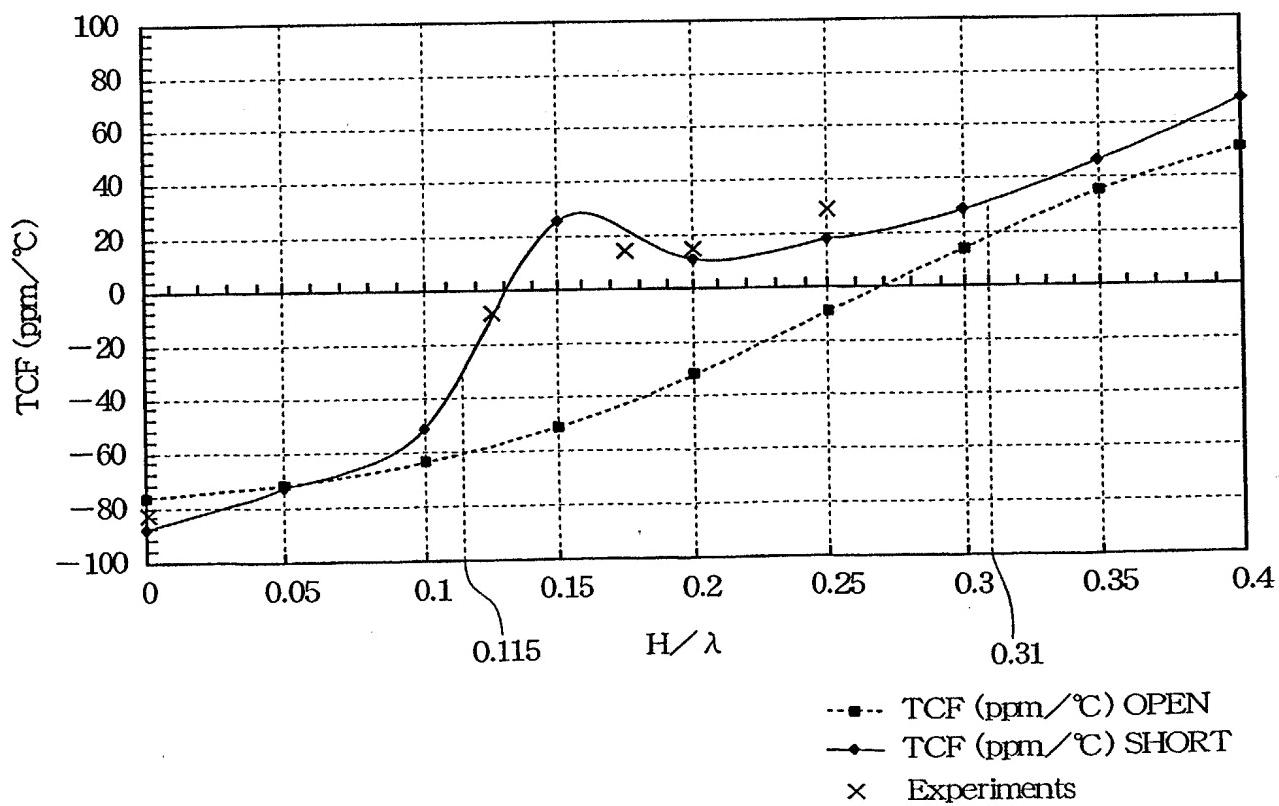


Fig.3

k^2 versus H/λ (film thickness of SiO_2) for the -10° to 40° rotated Y-cut, X-propagation LiNbO_3 substrate (Smith, 25°C)

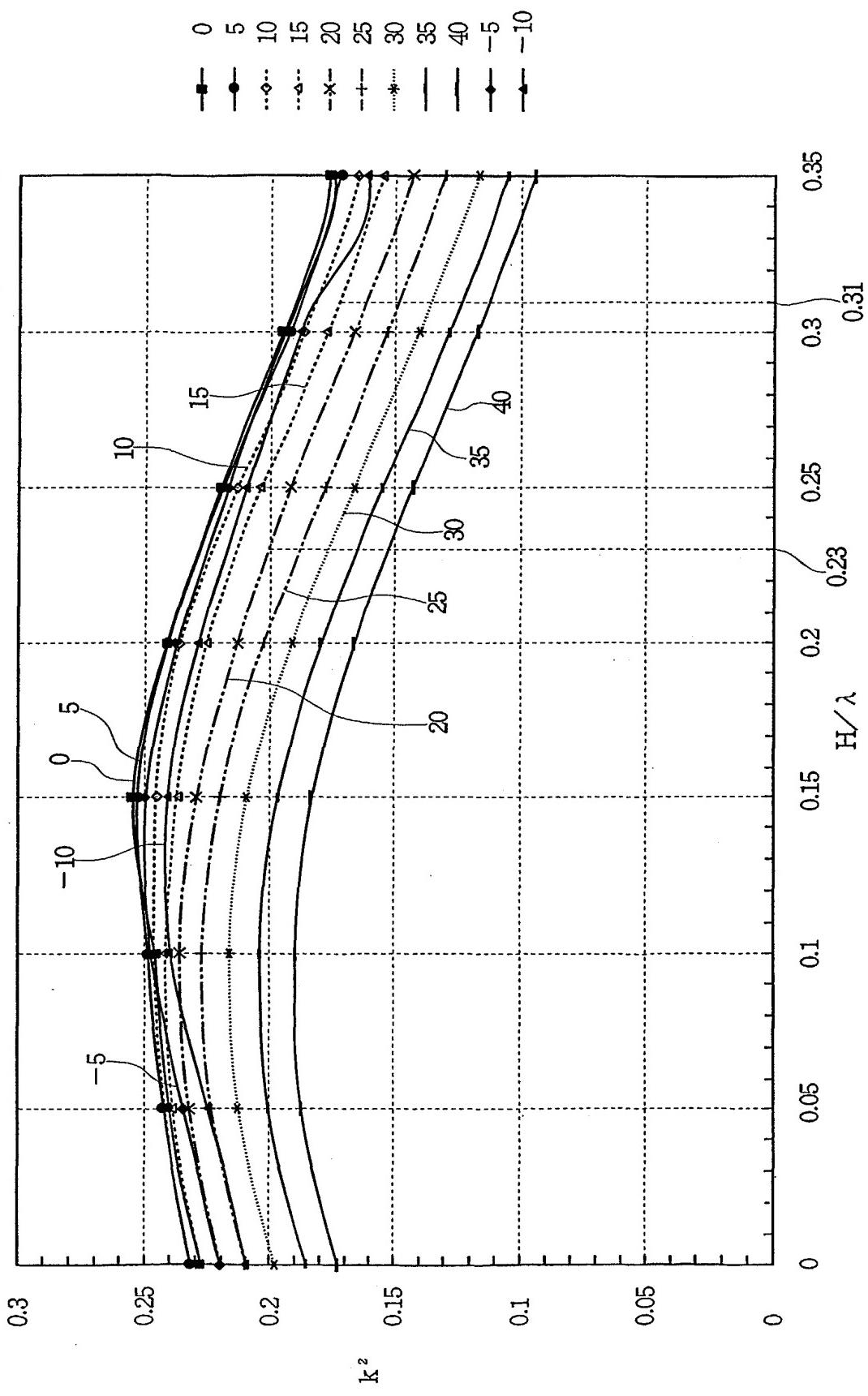


Fig.4
(10°)

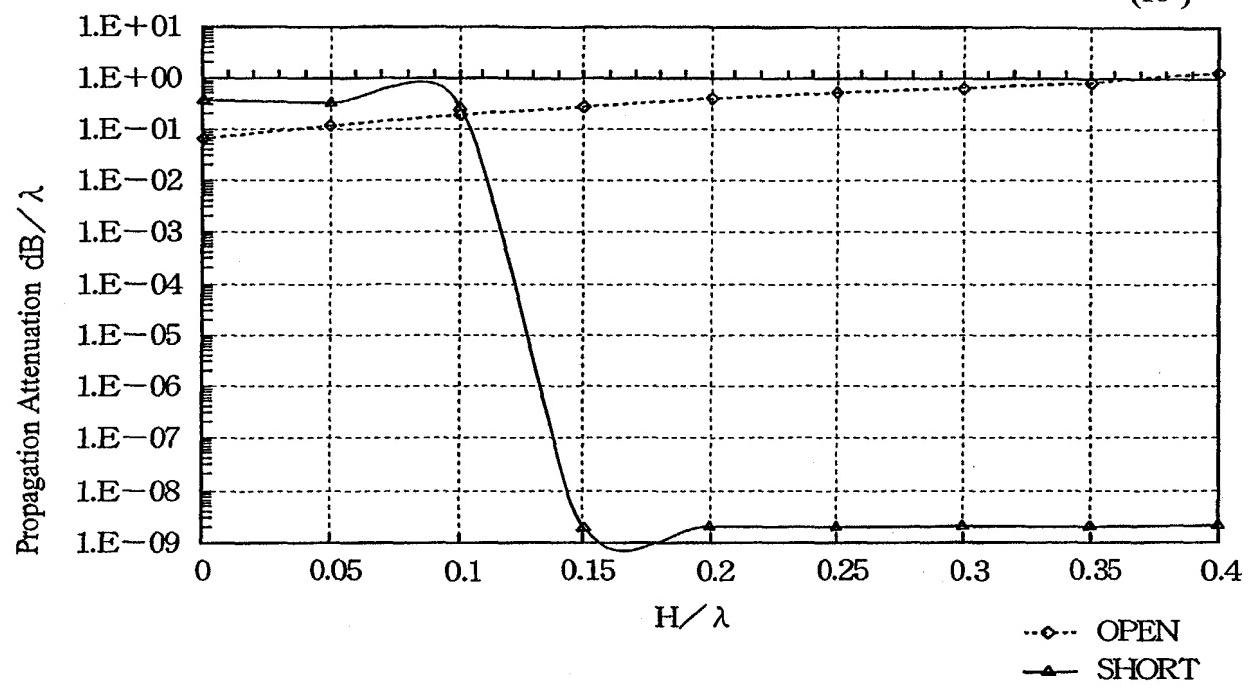


Fig.5
(0°)

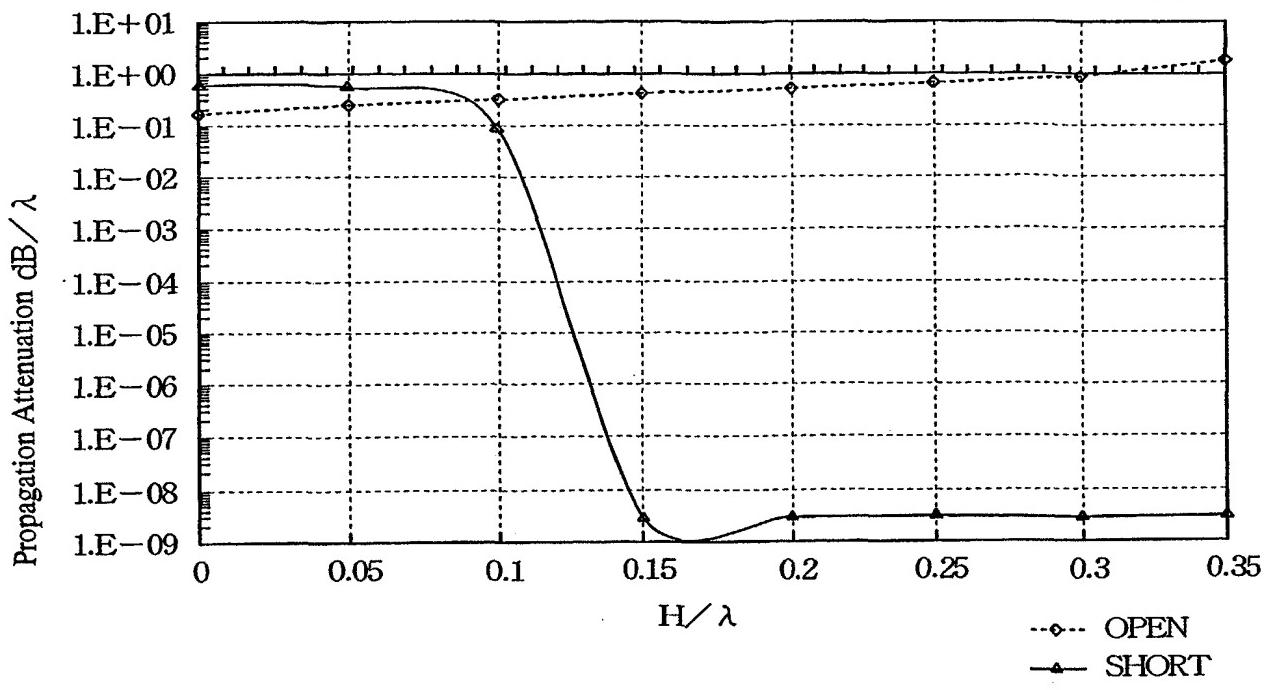
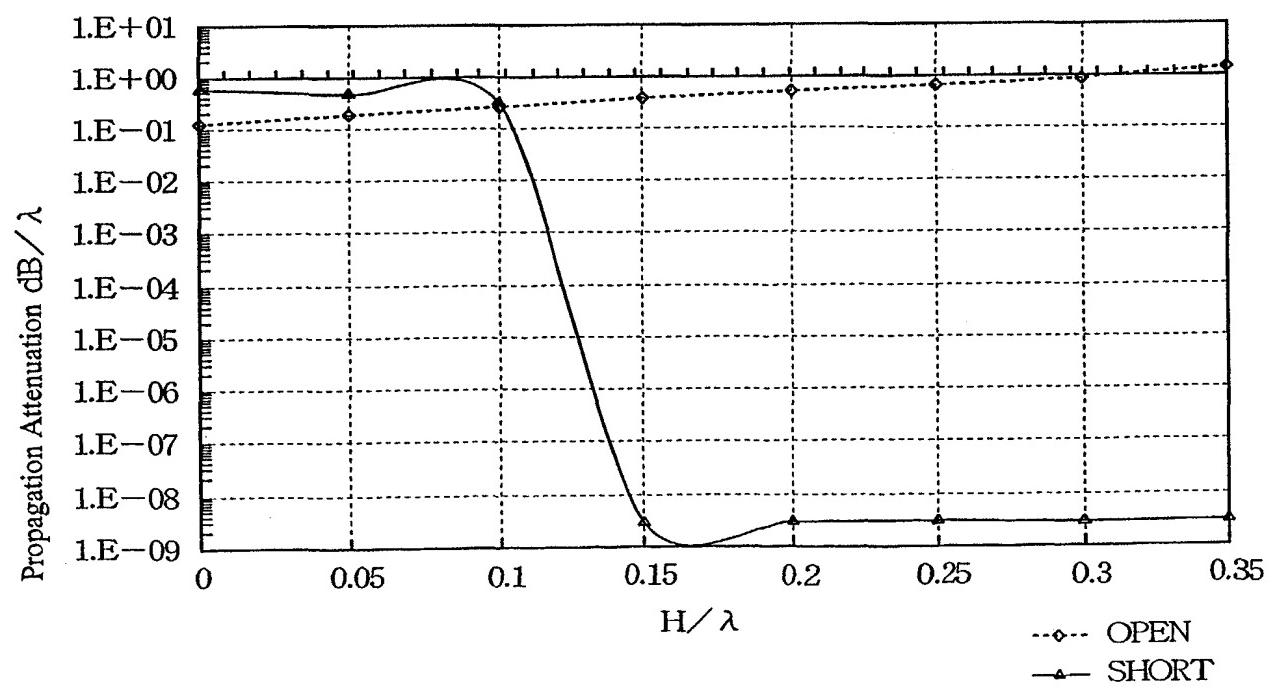


Fig.6
(5°)



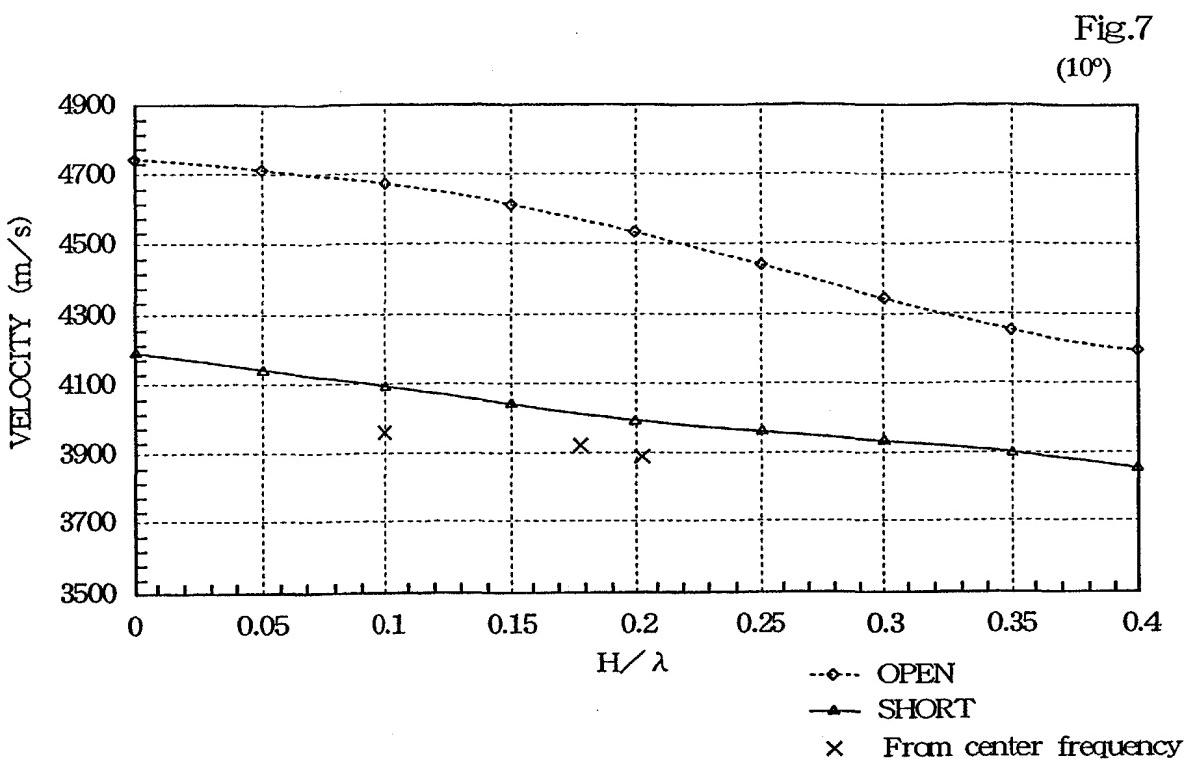


Fig.8

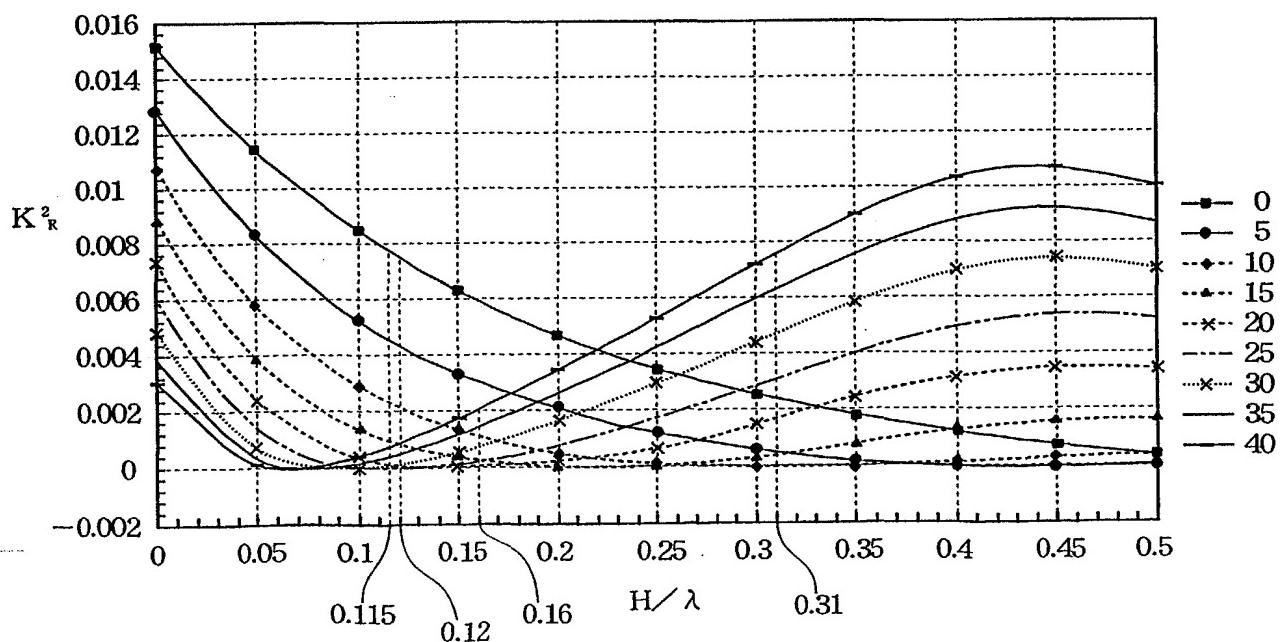


Fig.9

TCF (ppm/ $^{\circ}$ C) versus H/λ (film thickness of SiO_2) for SHORT of the 0° to 40° rotated Y-cut, X-propagation LiNbO_3 substrate (Smith constant)

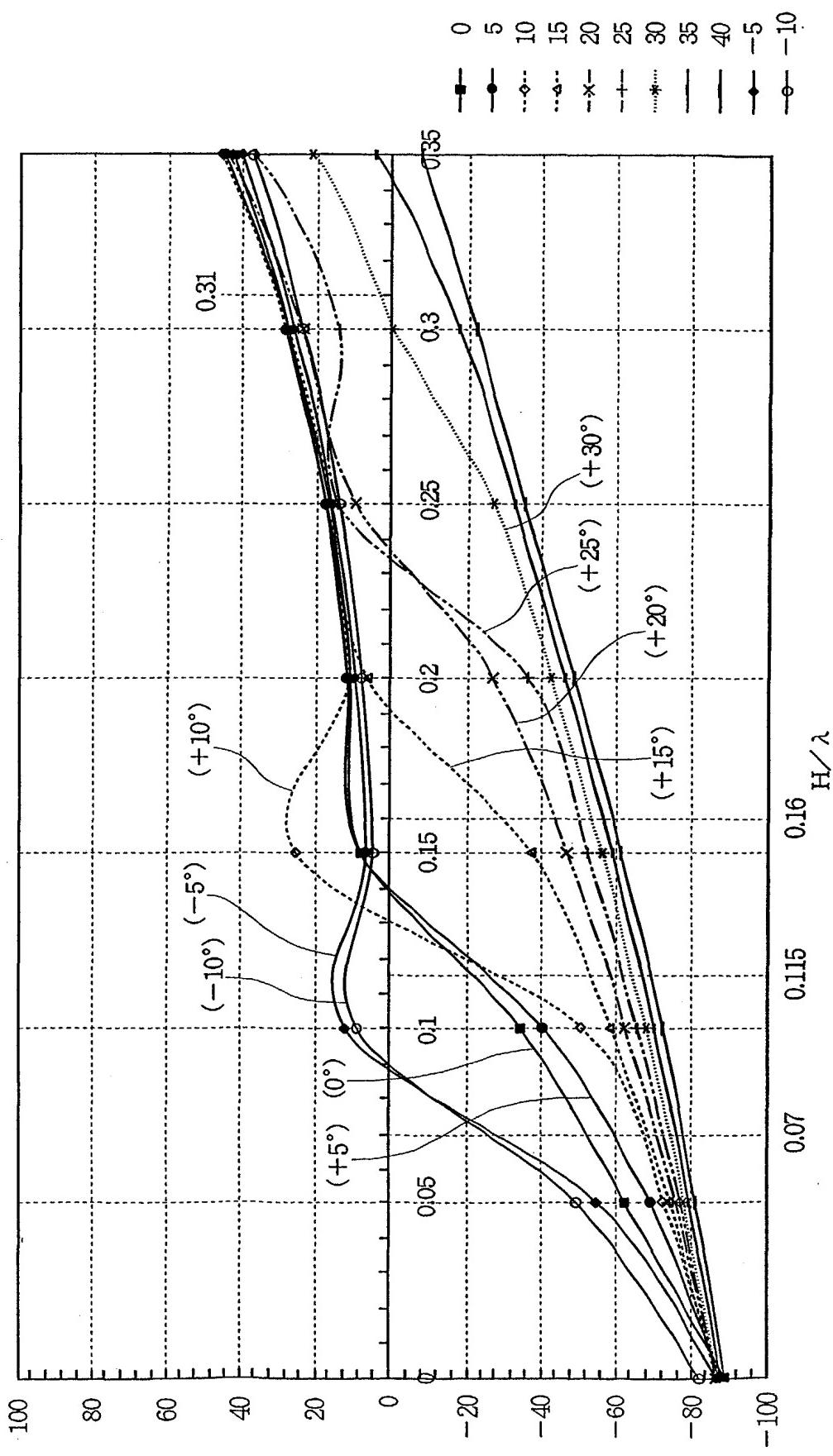
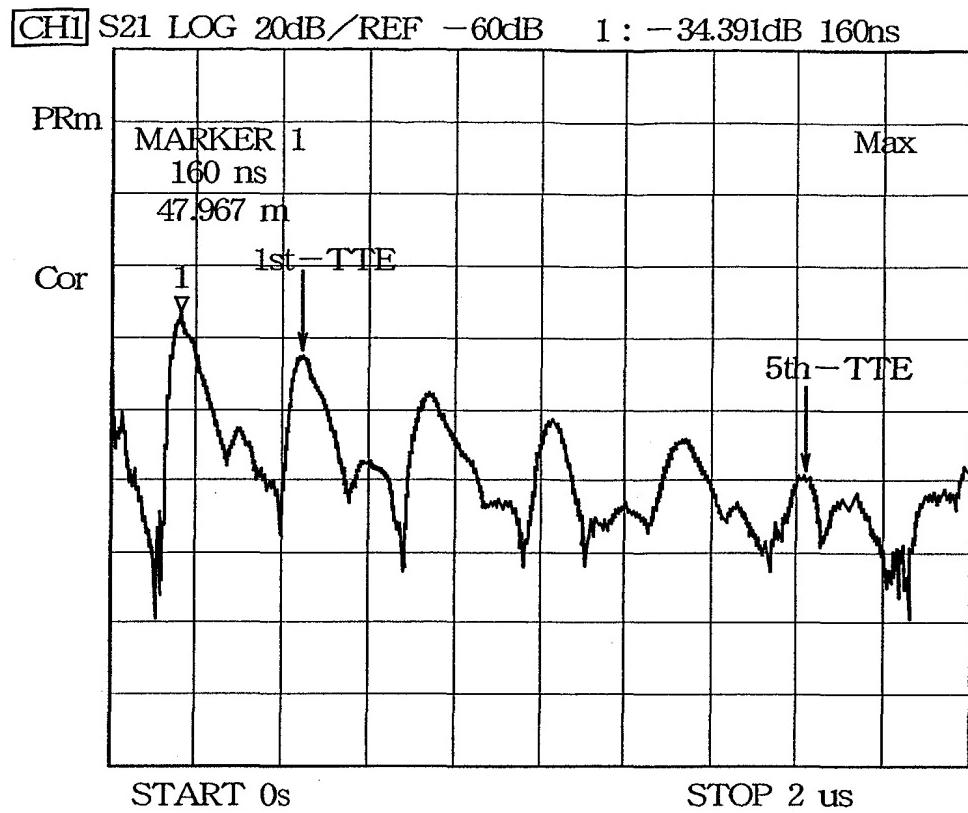


Fig.10



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Fig.11

